Low-power dual buffer with open-drain output Rev. 03 — 16 October 2007

Product data sheet

General description 1.

The 74AUP2G07 provides two non-inverting buffers with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. **Features**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114E Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Low static-power consumption; $I_{CC} = 0.9 \,\mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power dual buffer with open-drain output

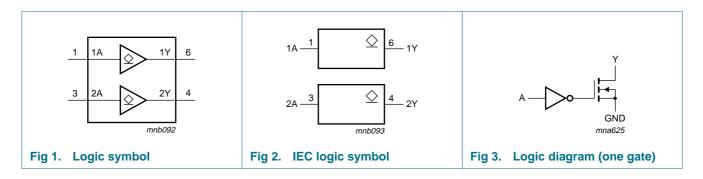
3. Ordering information

Table 1. Ordering information								
Type number	Package							
	Temperature range	Name	Description	Version				
74AUP2G07GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363				
74AUP2G07GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886				
74AUP2G07GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891				

4. Marking

Table 2. Marking	
Type number	Marking code
74AUP2G07GW	р7
74AUP2G07GM	р7
74AUP2G07GF	р7

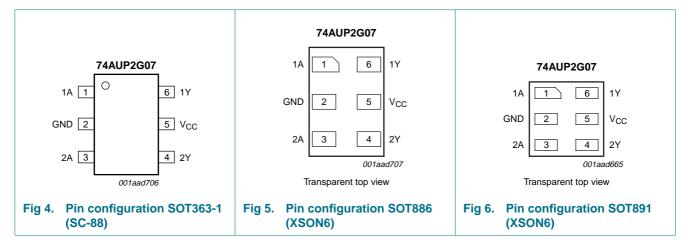
5. Functional diagram



Low-power dual buffer with open-drain output

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V _{CC}	5	supply voltage
1Y	6	data output

7. Functional description

Table 4.Function table^[1]

Input	Output
nA	nY
L	L
Н	Z

[1] H = HIGH voltage level;

L = LOW voltage level;

Z = high-impedance OFF state.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-	-50	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 package: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 0.	Recommended operating conditi	0115			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode and Power-down mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V$ to 3.6 V	0	200	ns/V

Table 6. Recommended operating conditions

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
VIL	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
lı –	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μΑ
I _{OZ}	OFF-state output current	$V_{I} = V_{IH}$; $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
ΔI_{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μA
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.7	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	0.9	-	pF
T _{amb} = -	40 °C to +85 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{CC}$	V
	. 5	V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V

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Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
lı	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μΑ
l _{oz}	OFF-state output current	$V_{I} = V_{IH}$; $V_{O} = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	$ V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V}; $	-	-	±0.6	μA
lcc	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = O \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	0.9	μA
∆l _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
T _{amb} = –	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.75 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V}$ to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I_{O} = 1.1 mA; V_{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		I_{O} = 1.7 mA; V_{CC} = 1.4 V	-	-	0.41	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.39	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.50	V
I	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
oz	OFF-state output current	V_{I} = $V_{IH};$ V_{O} = 0 V to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μA
OFF	power-off leakage current	$V_{\rm I}~{\rm or}~V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V	-	-	±0.75	μΑ

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At recomi	At recommended operating conditions; voltages are referenced to GND (ground = 0 V).						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μΑ	
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; I_{O} = O \; A; \\ V_{CC} = 0.8 \; V \; to \; 3.6 \; V \end{array}$	-	-	1.4	μA	
ΔI_{CC}	additional supply current	V_{I} = V_{CC} – 0.6 V; I_{O} = 0 A; V_{CC} = 3.3 V	-	-	75	μΑ	

Table 7. Static characteristics ... continued

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		–40 °C to +125 °C			Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 p	F								
t _{pd}	propagation delay	nA to nY; see Figure 7							
		$V_{CC} = 0.8 V$	-	11.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.1	4.1	7.5	1.7	9.1	10.0	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.6	3.0	5.1	1.3	6.1	6.7	ns
		V_{CC} = 1.65 V to 1.95 V	1.6	2.7	4.0	1.2	5.0	5.5	ns
		V_{CC} = 2.3 V to 2.7 V	1.1	2.1	3.2	0.9	4.0	4.4	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.4	2.2	2.8	1.1	3.3	3.6	ns
C _L = 10	pF								
t _{pd}	propagation delay	nA to nY; see Figure 7	l						
		$V_{CC} = 0.8 V$	-	14.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.0	5.1	9.0	2.4	11.2	12.3	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.3	3.8	6.1	2.0	7.4	8.1	ns
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	2.4	3.6	4.8	1.8	6.1	6.7	ns
		V_{CC} = 2.3 V to 2.7 V	1.7	2.8	3.8	1.3	4.8	5.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.2	3.1	4.2	1.6	4.5	5.0	ns
C _L = 15	pF								
t _{pd}	propagation delay	nA to nY; see Figure 7	l						
		$V_{CC} = 0.8 V$	-	17.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.5	6.1	10.4	3.2	13.1	14.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	3.0	4.5	6.8	2.6	8.6	9.4	ns
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	2.8	4.4	6.7	2.2	7.8	8.6	ns
		V_{CC} = 2.3 V to 2.7 V	2.4	3.4	4.5	1.9	5.3	5.8	ns
		V_{CC} = 3.0 V to 3.6 V	2.2	4.0	5.7	1.9	6.1	6.7	ns

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Symbol	Parameter	Conditions		25 °C		–40 °C to +125 °C			Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Мах (85 °С)	Max (125 °C)	
C _L = 30	pF								
t _{pd}	propagation delay	nA to nY; see Figure 7	[2]						
		$V_{CC} = 0.8 V$	-	26.7	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	4.8	9.0	15.6	4.3	18.8	20.7	ns
		V_{CC} = 1.4 V to 1.6 V	4.1	6.7	9.4	3.7	11.8	13.0	ns
		V_{CC} = 1.65 V to 1.95 V	3.8	6.8	9.7	3.2	11.0	12.1	ns
		V_{CC} = 2.3 V to 2.7 V	3.7	5.2	6.7	3.0	7.1	7.8	ns
		V_{CC} = 3.0 V to 3.6 V	3.6	6.4	9.7	2.8	10.4	11.4	ns
C _L = 5 p	F, 10 pF, 15 pF and	30 pF							
C _{PD}	power dissipation	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}}$	3][4]						
	capacitance	$V_{CC} = 0.8 V$	-	0.5	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V	-	0.6	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V	-	0.6	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V	-	0.7	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	0.9	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	1.2	-	-	-	-	pF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

[1] All typical values are measured at nominal V_{CC} .

 $\label{eq:tpd} \ensuremath{\left[2\right]} \quad t_{pd} \mbox{ is the same as } t_{PZL} \mbox{ and } t_{PLZ}.$

[3] All specified values are the average typical values over all stated loads.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 $f_i = input frequency in MHz;$

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

Low-power dual buffer with open-drain output

12. Waveforms

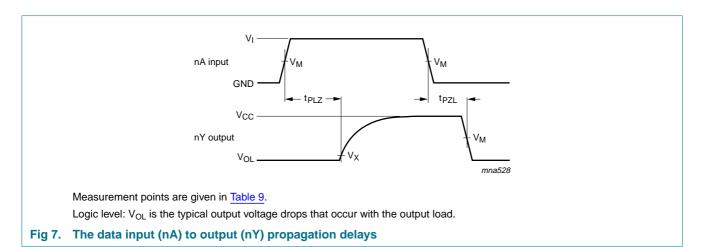


Table 9.Measurement points

Supply voltage	Input	Output	
V _{CC}	V _M	V _M	Vx
0.8 V to 1.6 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{OL} + 0.1 V
1.65 V to 2.7 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{OL} + 0.15 V
3.0 V to 3.6 V	$0.5 imes V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3 V$

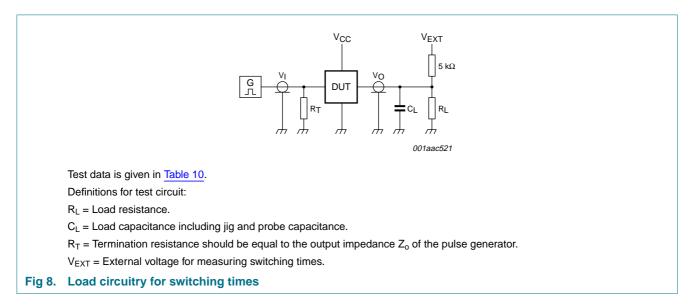


Table 10. Test data

Supply voltage	pply voltage Input		Load		V _{EXT}		
V _{cc}	VI	t _r , t _f	CL	RL ^[1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	V _{CC}	≤ 3 ns	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 \text{ k}\Omega$, for measuring propagation delays, set-up and hold times and pulse width $R_L = 1 \text{ M}\Omega$.

NXP Semiconductors

74AUP2G07

Low-power dual buffer with open-drain output

13. Package outline

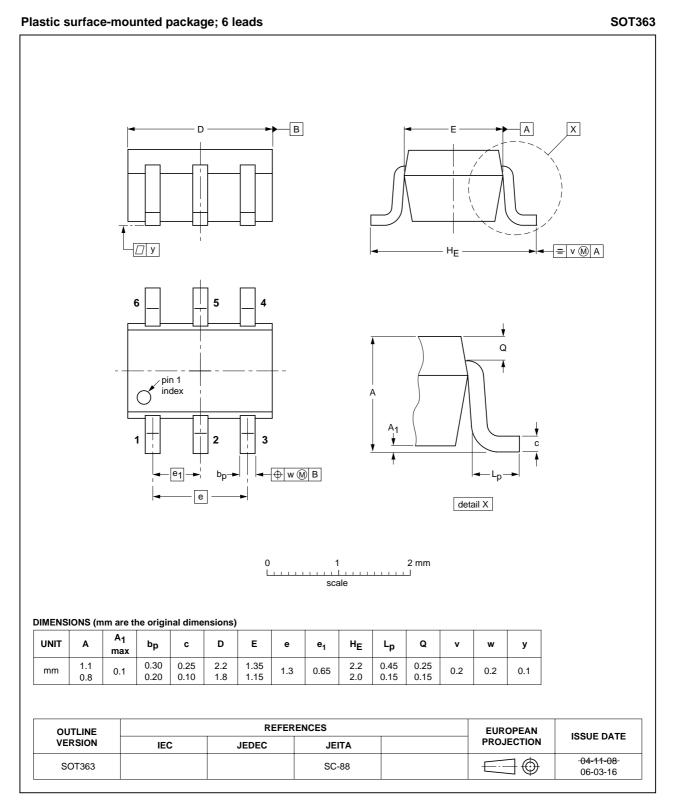


Fig 9. Package outline SOT363 (SC-88)

Low-power dual buffer with open-drain output

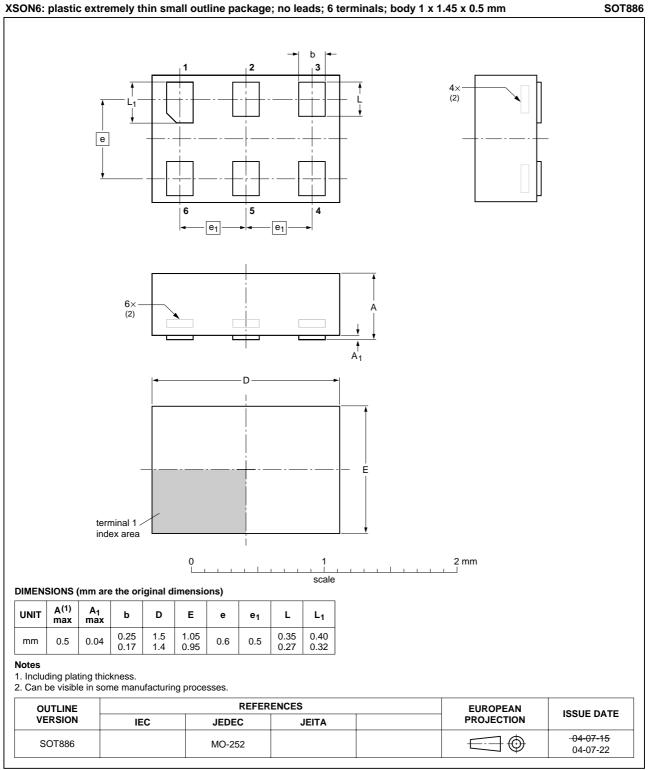


Fig 10. Package outline SOT886 (XSON6)

74AUP2G07_3 **Product data sheet**

Low-power dual buffer with open-drain output

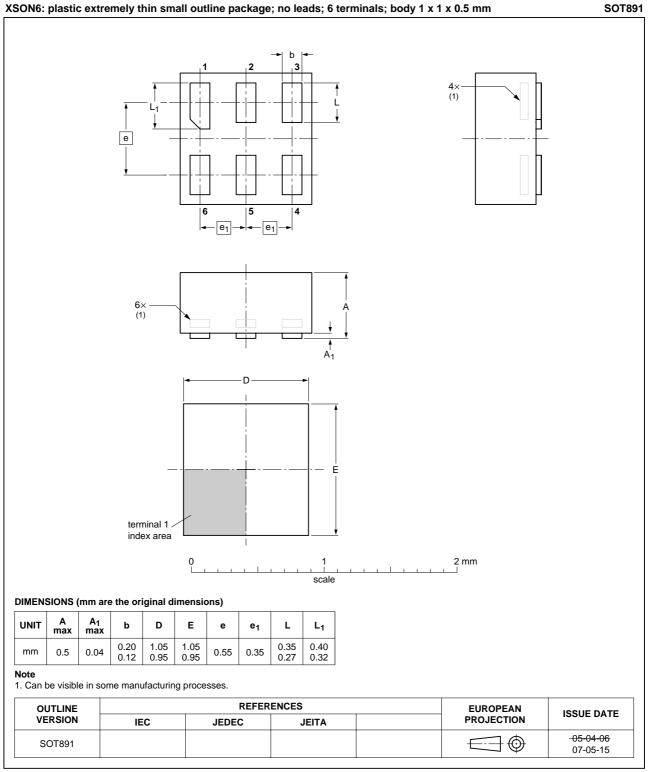


Fig 11. Package outline SOT891 (XSON6)

Low-power dual buffer with open-drain output

14. Abbreviations

AcronymDescriptionCDMCharged Device ModelCMOSComplementary Metal Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	Table 11.	e 11. Abbreviations		
CMOSComplementary Metal Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	Acronym	Description		
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	CDM	Charged Device Model		
ESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	CMOS	Complementary Metal Oxide Semiconductor		
HBM Human Body Model MM Machine Model	DUT	Device Under Test		
MM Machine Model	ESD	ElectroStatic Discharge		
	HBM	Human Body Model		
	MM	Machine Model		
IIL Iransistor-Iransistor Logic	TTL	Transistor-Transistor Logic		

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G07_3	20071016	Product data sheet	-	74AUP2G07_2
Modifications:		ies for C _I and C _O have change C _{PD} values have changed.	ed.	
74AUP2G07_2	20070612	Product data sheet	-	74AUP2G07_1
Modifications:	 Added I_{OZ} in 	Section 10 and Table 7		
74AUP2G07_1	20061121	Product data sheet	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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